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Product data sheet

1. General description

High voltage, high speed, planar passivated NPN power switching transistor with integrated antiparallel E-C diode in a SOT428 (DPAK) surface-mountable plastic package.

2. Features and benefits

- Fast switching
- High voltage capability
- Integrated anti-parallel E-C diode
- Surface mountable package
- · Very low switching and conduction losses

3. Applications

- DC-to-DC converters
- Electronic lighting ballasts
- Inverters
- Motor control systems

4. Pinning information

Table 1. Pinning information								
Pin	Symbol	Description	Simplified outline	Graphic symbol				
1	В	base	mb	Ç				
2	С	collector[1]						
3	E	emitter		B f				
mb	С	mounting base; connected to collector	DPAK (SOT428)	L E sym131				

[1] it is not possible to make a connection to pin 2 of the SOT428 (DPAK) package

NPN power transistor with integrated diode

5. Ordering information

Table 2. Ordering infor	mation				
Type number	Package				
	Name	Description	Version		
BUJD203AD	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428		

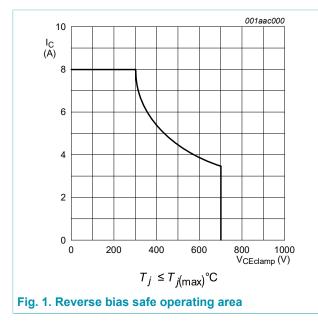
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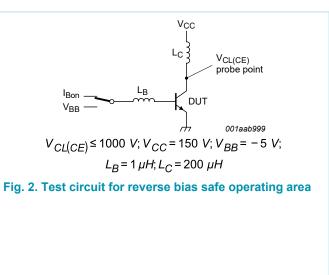
6. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

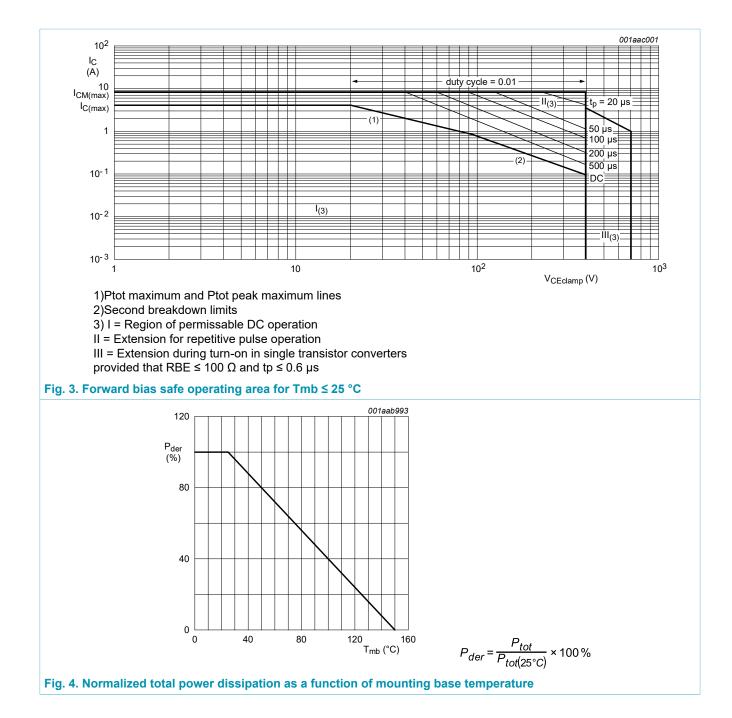
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V	-	850	V
V _{CBO}	collector-base voltage	I _E = 0 A	-	850	V
V _{CEO}	collector-emitter voltage	I _B = 0 A	-	425	V
I _C	collector current	DC; Fig. 1; Fig. 2; Fig. 3	-	4	А
I _{CM}	peak collector current	Fig. 1; Fig. 2; Fig. 3	-	8	А
I _B	base current	DC	-	2	А
I _{BM}	peak base current		-	4	А
P _{tot}	total power dissipation	T _{mb} ≤ 25 °C; <u>Fig. 4</u>	-	80	W
T _{stg}	storage temperature		-65	150	°C
Tj	junction temperature		-	150	°C





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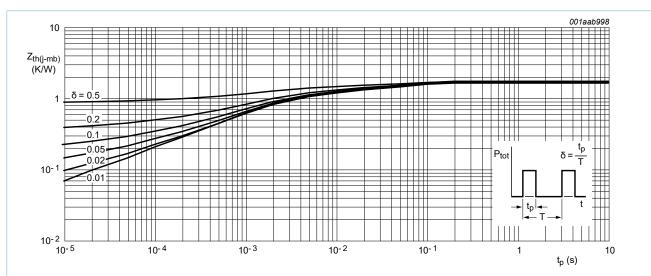


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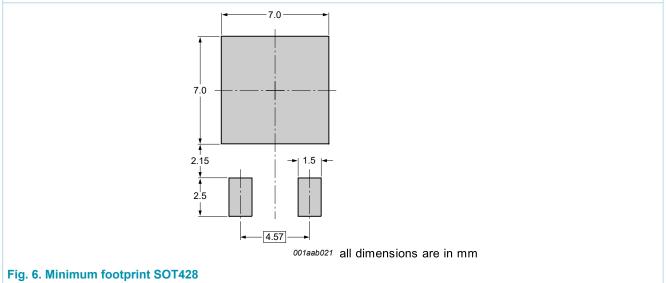
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7. Thermal characteristics

Table 4. Thermal characteristics								
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>		-	-	1.56	K/W	
R _{th(j-a)}	thermal resistance from junction to ambient free air	printed circuit board (FR4) mounted; minimum footprint; <u>Fig. 6</u>		-	75	-	K/W	







NPN power transistor with integrated diode

8. Characteristics

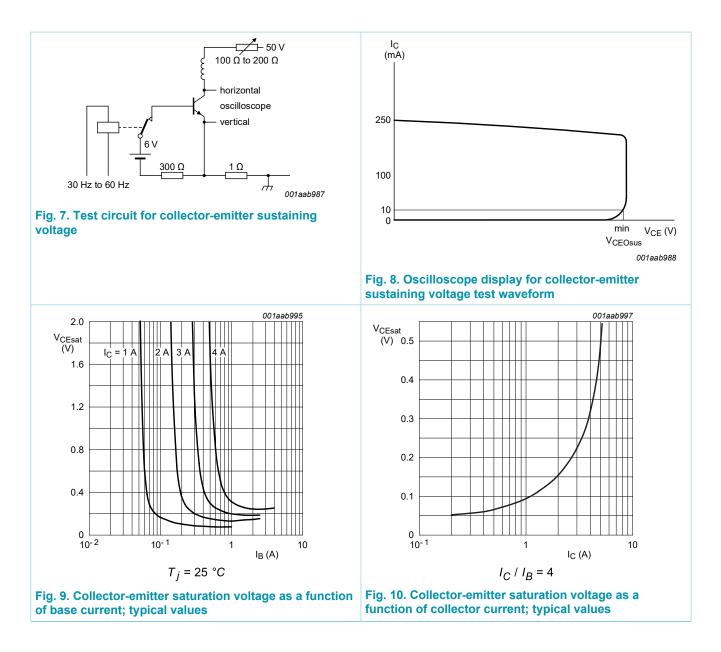
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static chara	acteristics						_
I _{CES}	collector-emitter cut-off	V _{BE} = 0 V; V _{CE} = 850 V; T _j = 125 °C	[1]	-	-	2	mA
	current (base shorted)	V _{BE} = 0 V; V _{CE} = 850 V; T _j = 25 °C	[1]	-	-	1	mA
I _{CBO}	collector-base cut-off current (emitter open)	V _{CB} = 850 V; I _E = 0 A	[1]	-	-	1	mA
I _{CEO}	collector-emitter cut-off current (base open)	V _{CE} = 425 V; I _B = 0 A	[1]	-	-	0.1	mA
I _{EBO}	emitter-base cut-off current (collector open)	V _{EB} = 7 V; I _C = 0 A		-	-	10	mA
V _{CEOsus}	collector-emitter sustaining voltage (base open)	I _B = 0 A; I _C = 10 mA; L _C = 25 mH; <u>Fig. 7; Fig. 8</u>		400	450	-	V
V _{CEsat}	collector-emitter saturation voltage	I _C = 3 A; I _B = 0.6 A; <u>Fig. 9; Fig. 10</u>		-	0.29	1	V
V _{BEsat}	base-emitter saturation voltage	I _C = 3 A; I _B = 0.6 A; <u>Fig. 11</u>		-	0.99	1.5	V
V _F	forward voltage	I _F = 2 A; T _j = 25 °C		-	1.04	1.5	V
h _{FE}	DC current gain	I _C = 1 mA; V _{CE} = 5 V; T _{mb} = 25 °C; <u>Fig. 12</u>		10	15	32	
		I _C = 500 mA; V _{CE} = 5 V; T _{mb} = 25 °C; <u>Fig. 12</u>		13	21	32	
		I _C = 2 A; V _{CE} = 5 V; T _{mb} = 25 °C; <u>Fig. 12</u>		11	16	22	
		I _C = 3 A; V _{CE} = 5 V; T _{mb} = 25 °C; <u>Fig. 12</u>		-	12.5	-	
Dynamic ch	aracteristics						
t _{on}	turn-on time	I _C = 2.5 A; I _{Bon} = 0.5 A; I _{Boff} = -0.5 A;		-	0.52	0.6	μs
t _s	storage time	R _L = 75 Ω; T _j = 25 °C; resistive load; Fig. 13; Fig. 14		-	2.7	3.3	μs
		$\begin{array}{l} {\sf I}_{C} = 2 \; {\sf A}; \; {\sf I}_{Bon} = 0.4 \; {\sf A}; \; {\sf V}_{BB} = -5 \; {\sf V}; \\ {\sf L}_{B} = 1 \; \mu {\sf H}; \; {\sf T}_{j} = 25 \; {}^{\circ}{\sf C}; \; {\sf inductive load}; \\ \hline {\sf Fig. \; 15}; \; {\sf Fig. \; 16} \end{array}$		-	1.2	1.4	μs
		$ I_C = 2 \text{ A}; I_{Bon} = 0.4 \text{ A}; V_{BB} = -5 \text{ V}; \\ L_B = 1 \ \mu\text{H}; T_j = 100 \ ^\circ\text{C}; \text{ inductive load}; \\ Fig. 15; Fig. 16 $		-	-	1.8	μs
t _f	fall time	$I_{C} = 2.5 \text{ A}; I_{Bon} = 0.5 \text{ A}; I_{Boff} = -0.5 \text{ A}; R_{L} = 75 \Omega; \text{ resistive load}; Fig. 13; Fig. 14$		-	0.3	0.35	μs
		I _C = 2 A; I _{Bon} = 0.4 A; V _{BB} = -5 V;		-	-	0.12	μs
		L _B = 1 μH; inductive load; <u>Fig. 15;</u> <u>Fig. 16</u>		-	0.03	0.06	μs

[1] Measured with half-sine wave voltage (curve tracer)

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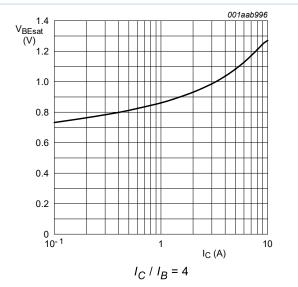
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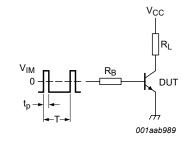
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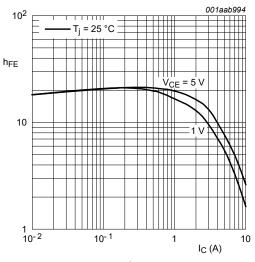
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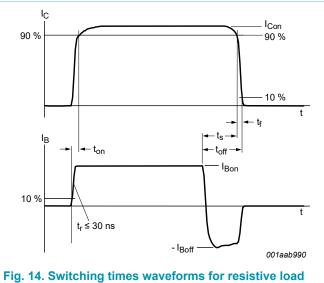


 $V_{IM} = -6$ to +8 V; $V_{CC} = 250$ V; $t_p = 20 \ \mu$ s; $\delta = \frac{t_p}{T} = 0.01$ R_B and R_L calculated from I_{Con} and I_{Bon} requirements. Fig. 13. Test circuit for resistive load switching



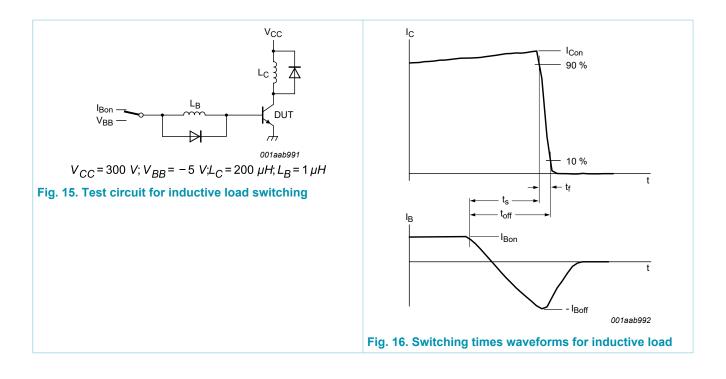






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9. Package outline

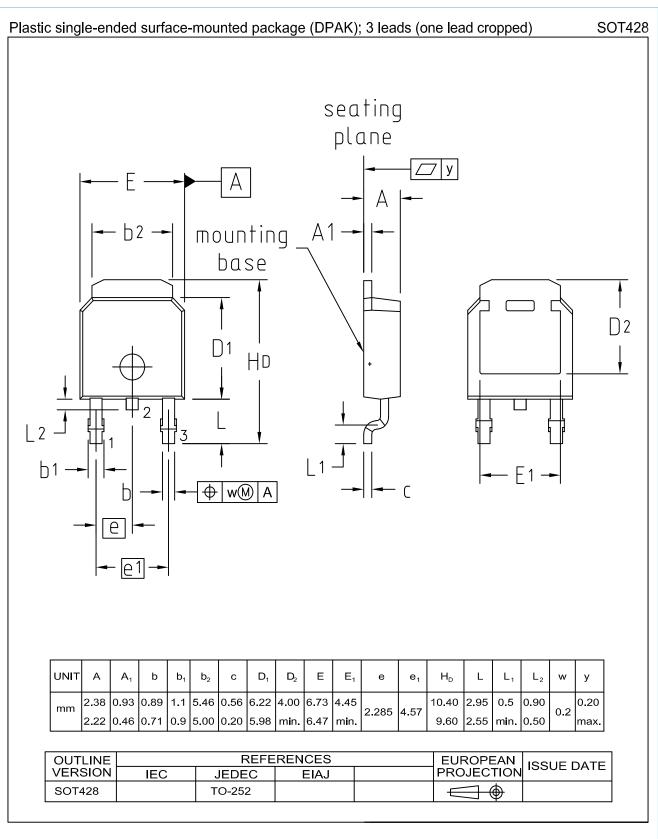


Fig. 17. Package outline DPAK (SOT428)
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Document status [1][2]	Product status [<u>3]</u>	Definition
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